

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for plasma treatment, comprising the steps of:

(a) arranging a substrate in a chamber, wherein the substrate includes an SiC layer and an SiO<sub>2</sub> layer; and

(b) introducing an etching gas into the chamber and converting the etching gas into plasma to etch selectively the SiC layer against the SiO<sub>2</sub> layer, wherein the etching gas includes CHF<sub>3</sub>, as a main fluorocarbon component thereof, and a material having N.

Claim 2 (Original): The method of claim 1, wherein the SiO<sub>2</sub> layer is a mask layer on the SiC layer, and wherein the mask layer has an opening pattern.

Claim 3 (Original): The method of claim 1, wherein the SiO<sub>2</sub> layer is a base layer of the SiC layer.

Claim 4 (Canceled):

Claim 5 (Currently Amended): The method of claim ~~[[4]]~~ 1, wherein the material having N is N<sub>2</sub>.

Claim 6 (Original): The method of claim 5, wherein a ratio of CHF<sub>3</sub> flow rate to N<sub>2</sub> flow rate in the etching gas is between about 0.2 and about 0.6.

Claim 7 (Original): The method of claim 5, wherein a ratio of CHF<sub>3</sub> flow rate with respect to N<sub>2</sub> flow rate in the etching gas is between about 0.4 and about 0.6.

Claim 8 (Currently Amended): ~~A method for plasma treatment~~ The method of claim 18, comprising the steps of:

~~(a) arranging a substrate in a chamber, wherein the substrate includes an SiC layer;~~  
and  
~~(b) introducing an etching gas having CHF<sub>3</sub> and N<sub>2</sub> into the chamber and converting the etching gas into plasma to etch the SiC layer.~~

wherein the material having C, H and F is CHF<sub>3</sub>, and the material having N is N<sub>2</sub>.

Claim 9 (Original): The method of claim 8, wherein a ratio of CHF<sub>3</sub> flow rate with respect to N<sub>2</sub> flow rate in the etching gas is between about 0.2 and about 0.8.

Claim 10 (Original): The method of claim 8, wherein a ratio of CHF<sub>3</sub> flow rate with respect to N<sub>2</sub> flow rate in the etching gas is between about 0.4 and about 0.8.

Claim 11 (Original): The method of claim 8, wherein a ratio of CHF<sub>3</sub> flow rate with respect to N<sub>2</sub> flow rate in the etching gas is between about 0.4 and about 0.6.

Claim 12 (Original): The method of claim 8, wherein the substrate includes an organic layer and the SiC layer is etched selectively against the organic layer.

Claim 13 (Original): The method of claim 12, wherein the organic layer is a mask layer of the SiC layer and the mask layer has an opening pattern.

Claim 14 (Original): The method of claim 12, wherein the organic layer is a base layer of the SiC layer.

Claim 15 (Original): The method of claim 12, wherein a ratio of CHF<sub>3</sub> flow rate with respect to N<sub>2</sub> flow rate in the etching gas is between about 0.2 and about 0.8.

Claim 16 (Original): The method of claim 12, wherein a ratio of CHF<sub>3</sub> flow rate with respect to N<sub>2</sub> flow rate in the etching gas is between about 0.4 and about 0.6.

Claim 17 (Original): The method of claim 12, wherein the organic layer is a dielectric layer with a lower dielectric constant.

Claim 18 (Currently Amended): A method for plasma treatment, comprising the steps of:

(a) arranging a substrate in a chamber, wherein the substrate includes an SiC layer;  
and

(b) introducing an etching gas into the chamber and converting the etching gas into plasma to etch the SiC layer, wherein the etching gas includes a material having C, H and F and a material having N, the etching gas being essentially free from any material having O, wherein the material having C, H and F is a main fluorocarbon component of the etching gas.

Claim 19 (Original): The method of claim 18, wherein the material having C, H and F is CHF<sub>3</sub>.

Claim 20 (Original): The method of claim 18, wherein the material having N is N<sub>2</sub>.

Claim 21 (Original): The method of claim 18, wherein the substrate includes an organic layer and the SiC layer is etched selectively against the organic layer.

Claim 22 (Original): The method of claim 21, wherein the material having C, H and F is CHF<sub>3</sub>.

Claim 23 (Original): The method of claim 21, wherein the material having N is N<sub>2</sub>.

Claim 24 (Original): The method of claim 21, wherein the organic layer is a dielectric layer with a lower dielectric constant.

Claim 25 (Original): The method of claim 18, wherein the substrate includes a SiO<sub>2</sub> layer and the SiC layer is etched selectively against the SiO<sub>2</sub> layer.

Claim 26 (Original): The method of claim 25, wherein the material having C, H and F is CHF<sub>3</sub>.

Claim 27 (Original): The method of claim 25, wherein the material having N is N<sub>2</sub>.

Claim 28 (Original): The method of claim 18, wherein a base layer of the SiC layer is a Cu layer.

Claim 29 (New): The method of claim 1, wherein the etching gas consists of  $\text{CHF}_3$ ,  $\text{N}_2$  and an inert gas.